



Attorney Docket 040301-0578

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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TC 2800 MAIL ROOM

Applicant: Nobutoshi AOKI et al.

Title: SEMICONDUCTOR INTEGRATED CIRCUIT INCLUDING  
INSULATED GATE FIELD EFFECT TRANSISTOR AND METHOD  
OF MANUFACTURING THE SAME

Appl. No.: 09/440,928

Filing Date: November 16, 1999

Examiner: S. Rao

Art Unit: 2814

1/Supp B  
step 1  
3-1902

**SUPPLEMENTAL  
AMENDMENT AND REPLY UNDER 37 C.F.R. § 1.111**

Commissioner for Patents  
Washington, D.C. 20231  
Box NON-FEE

Sir:

In further reply to the Office Action mailed November 26, 2001, and supplemental to the Amendment filed February 26, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend the claims by replacing the indicated claims with the following clean versions. (See Attachment A for the marked up version of the amended claims.)

1. (Twice Amended) A semiconductor device comprising:  
a pair of main electrodes used as source and drain electrodes;  
an insulating gate film adjacent to the pair of main electrodes; and  
a gate electrode comprising of a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region.

See C17  
B2